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Abstract : In recent years, the expansion of the Internet and advancements in the performance of electronic technology device has driven the demand for higher capacity and faster speeds in communication technologies. Beyond the traditional fourth-generation (4G) frequency bands, the advent of fifth-generation (5G) communication technology has brought into play new frequency bands in the millimeter wave region, notably at 20 GHz or higher. Consequently, developing heat-resistant materials with low dielectric properties for next-generation wireless communication devices has become crucial. Such materials are key to achieving faster communication speeds, enabling the connection of numerous devices simultaneously, and minimizing data processing delays.

The chemical structure shows a polyimide repeating unit. The core is a benzophenone derivative where the two phenyl rings are substituted with phenylsiloxy groups. The repeating unit is enclosed in brackets with a subscript n . The X group is defined as a phenyl ring substituted with a phenylsiloxy group and a methyl group, connected to the polymer backbone via the phenyl ring.

Figure 1. Chemical structure of double-decker silsesquioxane (DDSQ)-based polyimide

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